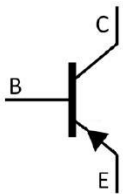


TO-126F PNP Silicon PNP transistor in a TO-126F Plastic Package.

I_C $V_{CE(sat)}$
 High I_C , low $V_{CE(sat)}$.

Strobe flash applications, audio power amplifier applications.

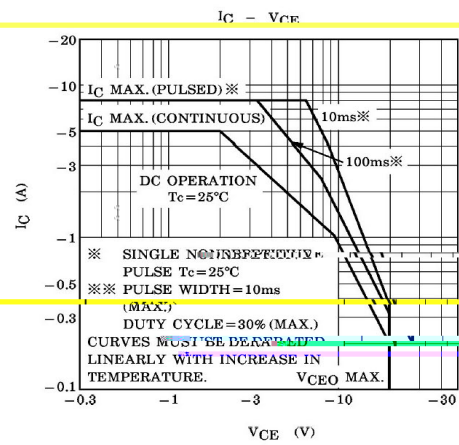
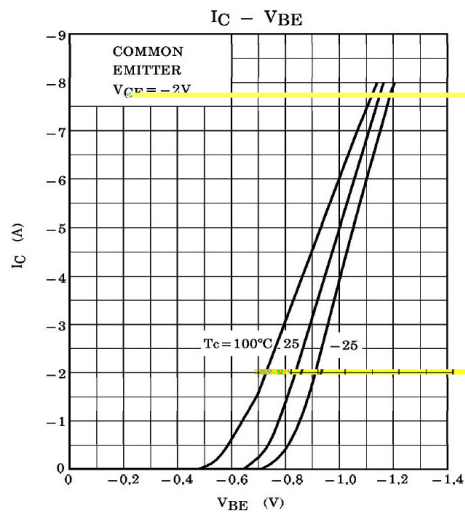
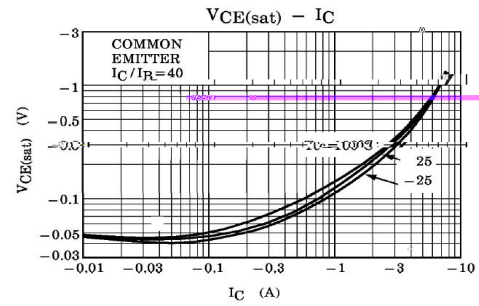
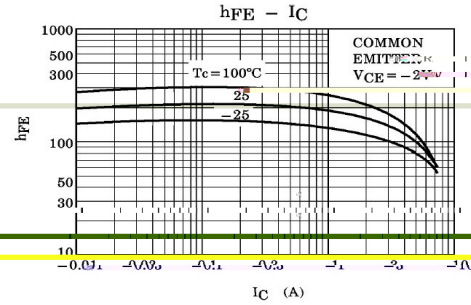
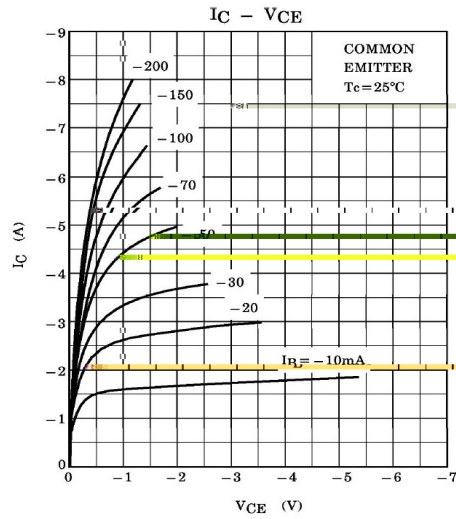


PIN1 Emitter PIN 2 Collector PIN 3 Base

h_{FE} Classifications Symbol	O	Y
h_{FE} Range	100 200	160 320

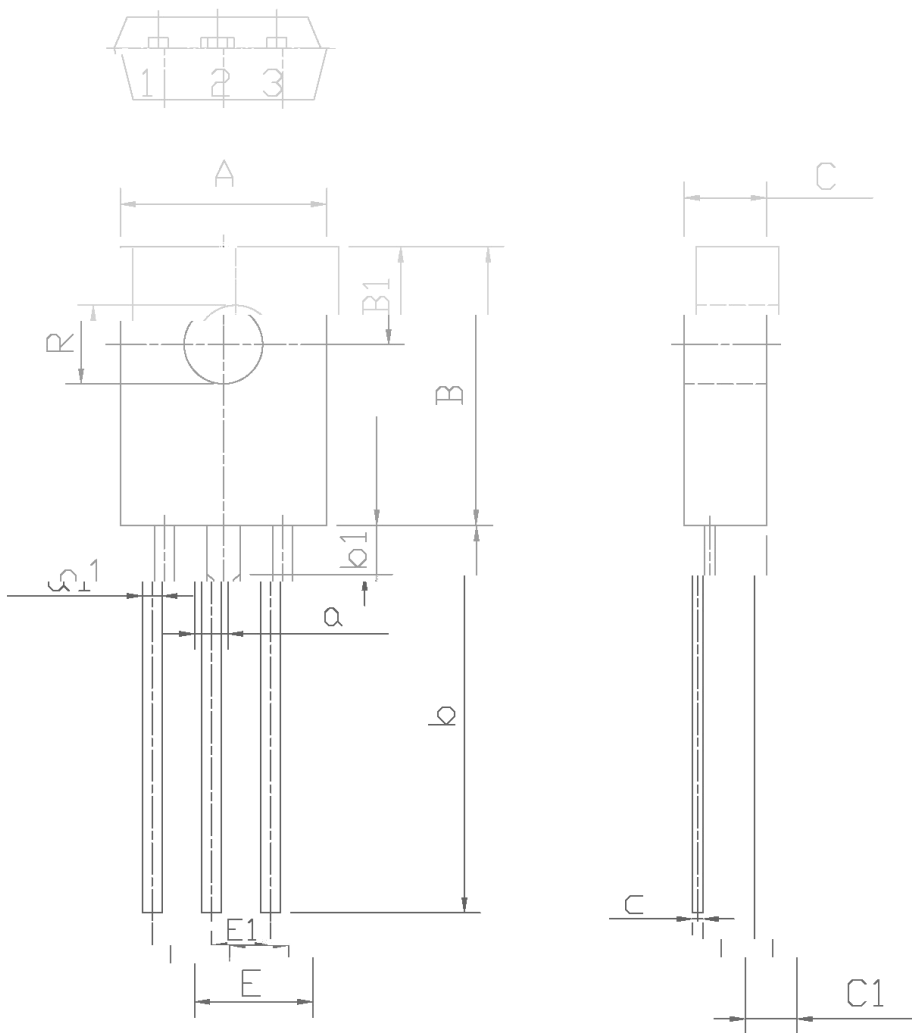
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	-35	V
Collector to Emitter Voltage	V_{CEO}	-20	V
Emitter to Base Voltage	V_{EBO}	-8.0	V
Collector Current - Continuous	I_C	-5.0	A
Collector Current – Continuous(Pulse)	I_{CP}	-8.0	A
Base Current – Continuous	I_B	-1.0	A
Collector Power Dissipation	P_C	1.5	W
Collector Power Dissipation	$P_C(T_C=25^\circ\text{C})$	10	W
Junction Temperature	T_J	150	
Storage Temperature Range	T_{stg}	-55 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector to Emitter Breakdown Voltage	V					

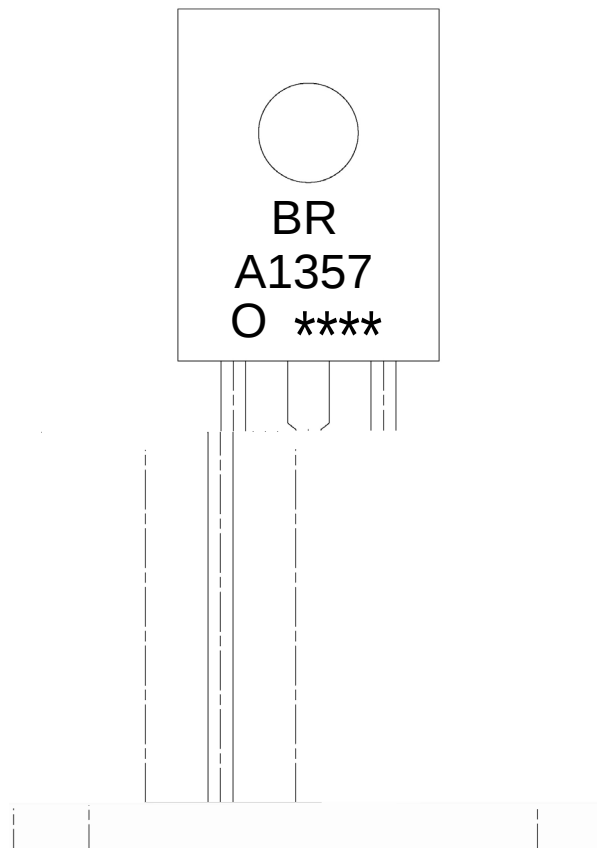


FW-126T

单位: mm



Symbol	Dimension in Millimeters		Symbol	Dimension in Millimeters	
	Min	Max		Min	Max
A	7.8	8.2	a1	0.55	0.85
B	10.8	11.2	E	4.4	4.8
B1	3.8	4.2	C	3.1	3.3
R	2.95	3.15	C1	1.9	2.1
b	14	16	c	0.3	0.6
b1	1.9		a	1.27	
E1	2.1	2.5			



BR

A1357

O: h_{FE}

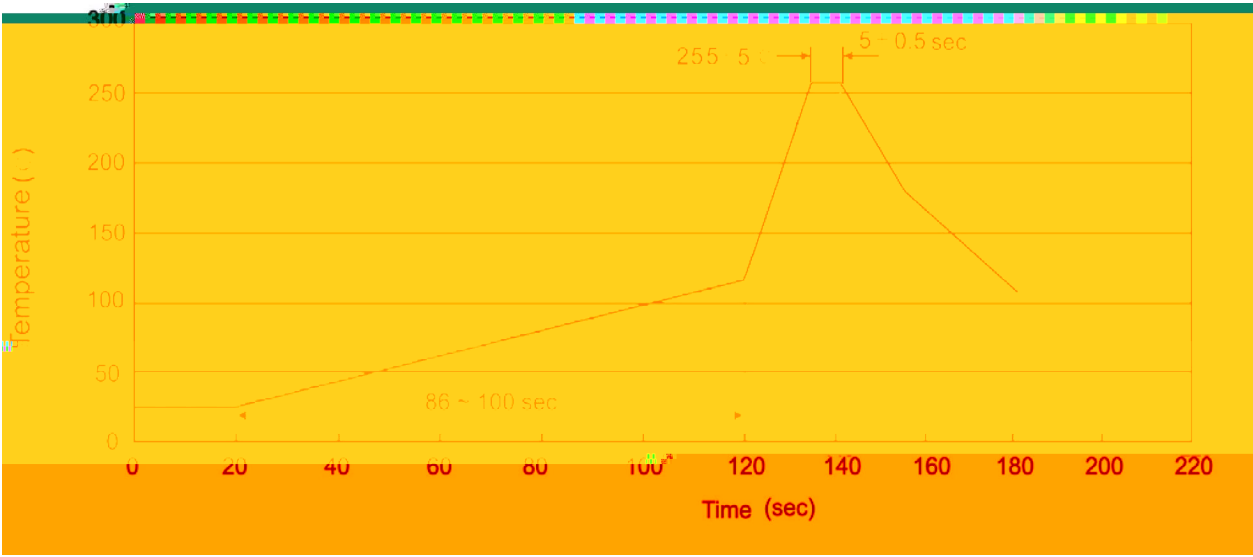
Note:

BR: Company Code

A1357: Product Type.

O: h_{FE} Classifications Symbol

****: Lot No. Code, code change with Lot No.



- 1

25 150

60 90sec;
- 2

255±5

5±0.5sec;
- 3

2 10 /sec.
- Note:

1.Preheating:25~150 , Time:60~90sec.

2.Peak Temp.:255±5 , Duration:5±0.5sec.

3. Cooling Speed: 2~10 /sec.

270±5

10±1 sec.

Temp.:270±5

Time:10±1 sec

/ BULK

Package Type	Units		Dimension	(unit mm ³)
	Units/Tube	Tubes/Inner Box		
	/	/		